

3-V to 5.5-V Multichannel RS-232 Line Drivers and Receivers with ± 15 -kV ESD Protection

1 Features

- ESD Protection for RS-232 bus pins
 - ± 15 -kV Human-body model (HBM)
 - ± 8 -kV IEC 61000-4-2, Contact discharge
 - ± 15 -kV IEC 61000-4-2, Air-gap discharge
- Meet or exceed the requirements of TIA/EIA-232-F and ITU v.28 standards
- Operate with 3-V to 5.5-V V_{CC} supply
- Operate up to 1000 kbit/s
- Two drivers and two receivers
- Low standby current . . . 1 μ A Typ
- External capacitors . . . $4 \times 0.1 \mu$ F
- Accepts 5-V Logic Input with 3.3-V supply

2 Applications

- [Industrial PCs](#)
- [Wired Networking](#)
- [Data center and networking equipment](#)
- [Notebooks](#)
- [Hand-held equipment](#)

3 Description

The SN65C3222E and SN75C3222E consist of two line drivers, two line receivers, and a dual charge-pump circuit with ± 15 -kV ESD protection pin to pin (serial-port connection pins, including GND).

The devices meet the requirements of TIA/EIA-232-F and provide the electrical interface between

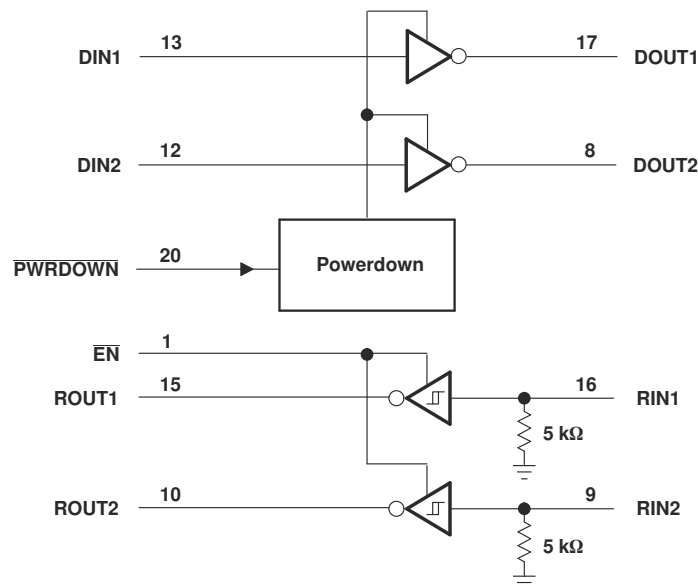
an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at typical data signaling rates up to 1000 kbit/s and are improved drop-in replacements for industry-popular '3222 two-driver, two-receiver functions.

The SN65C3222E and SN75C3222E can be placed in the power-down mode by setting the power-down (PWRDOWN) input low, which draws only 1 μ A from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; $V+$ is lowered to V_{CC} , and $V-$ is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable (\overline{EN}) high.

Device Information

| PART NUMBER | PACKAGE ⁽¹⁾ | BODY SIZE (NOM) |
|--------------------------|------------------------|-------------------|
| SN65C3222E SN75C3222E | DB (SSOP) (20) | 10.2 mm x 5.30 mm |
| | DW (SOIC) (20) | 15.4 mm x 7.50 mm |
| | PW (TSSOP) (20) | 7.80 mm v 4.40 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Pin numbers are for the DB, DW, and PW packages.

Logic Diagram (Positive Logic)



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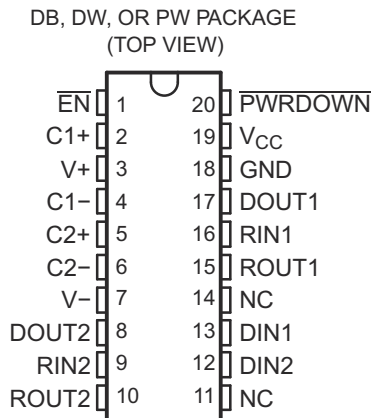
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| Changes from Revision A (July 2006) to Revision B (August 2021) | Page |
|--|-------------|
| • Updated the list of <i>Applications</i> | 1 |
| • Deleted the <i>Ordering Information</i> table. Removed the RHL package from the <i>Device Information</i> table..... | 1 |
| • Added the <i>Device Information</i> table, the <i>Pin Configuration and Functions</i> , the <i>Detailed Description</i> section, the <i>Application and Implementation</i> section..... | 1 |
| • Deleted the Package thermal impedance from the <i>Absolute Maximum Ratings</i> | 4 |
| • Added the <i>ESD Ratings</i> table..... | 4 |
| • Added the <i>Thermal Information: SN65C3222E</i> table..... | 5 |
| • Changed the value of $R_{\theta JA}$ for PW package (previously in the <i>Absolute Maximum Ratings</i> table), and added additional thermal parameters for all packages in the <i>Thermal Information: SN65C3222E</i> table..... | 5 |
| • Added separate <i>Thermal Information</i> table for SN75C3222E..... | 5 |

5 Pin Configuration and Functions



NC – No internal connection

Table 5-1. Pin Functions

| PIN | | I/O | DESCRIPTION |
|-----------------|-------|-----|-----------------------------|
| NAME | NO. | | |
| C1+ | 2 | — | Charge pump capacitor pin |
| C1- | 4 | — | Charge pump capacitor pin |
| C2+ | 5 | — | Charge pump capacitor pin |
| C2- | 6 | — | Charge pump capacitor pin |
| DIN1 | 13 | I | Driver logic input |
| DIN2 | 12 | I | Driver logic input |
| DOUT1 | 17 | O | RS-232 driver output |
| DOUT2 | 8 | O | RS-232 driver output |
| EN | 1 | I | Receiver enable, active low |
| GND | 18 | — | Ground |
| NC | 11,14 | — | No internal connection |
| PWRDOWN | 20 | I | Driver disable, active low |
| RIN1 | 16 | I | RS-232 receiver input |
| RIN2 | 9 | I | RS-232 receiver input |
| ROUT1 | 15 | O | Receiver logic output |
| ROUT2 | 10 | O | Receiver logic output |
| V _{CC} | 19 | — | Power Supply |
| V+ | 3 | — | Charge pump capacitor pin |
| V- | 7 | — | Charge pump capacitor pin |

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

| | | MIN | MAX | UNIT | |
|------------------|---|-----------------------|-------|-----------------------|---|
| V _{CC} | Supply voltage range ⁽²⁾ | -0.3 | 6 | V | |
| V+ | Positive-output supply voltage range ⁽²⁾ | -0.3 | 7 | V | |
| V- | Negative-output supply voltage range ⁽²⁾ | 0.3 | -7 | V | |
| V+ – V- | Supply voltage difference ⁽²⁾ | | 13 | V | |
| V _I | Input voltage range | Driver (EN, PWRDOWN) | -0.3 | 6 | V |
| | | Receiver | -25 | 25 | |
| V _O | Output voltage range | Driver | -13.2 | 13.2 | V |
| | | Receiver | -0.3 | V _{CC} + 0.3 | |
| T _J | Operating virtual junction temperature | | 150 | °C | |
| T _{stg} | Storage temperature range | -65 | 150 | °C | |

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network GND.

6.2 ESD Ratings

| | | | VALUE | UNIT |
|--------------------|-------------------------|---|---------|------|
| V _(ESD) | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ | ±3,000 | V |
| | | | ±15,000 | |
| | | Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾ | ±1,500 | |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings - IEC Specifications

| | | | VALUE | UNIT |
|--------------------|-------------------------|---|---------|------|
| V _(ESD) | Electrostatic discharge | IEC 61000-4-2, Contact Discharge ⁽¹⁾ | ±8,000 | V |
| | | IEC 61000-4-2, Air Discharge ⁽¹⁾ | ±15,000 | |

- (1) For the PW Package of SN65C3222E only, a minimum of 1-μF capacitor is required between V_{CC} and GND to meet the specified IEC 61000-4-2 rating

6.4 Recommended Operating Conditions

See [Figure 9-1](#) and ⁽¹⁾

| | | | MIN | NOM | MAX | UNIT |
|----------------|---|---|-------------------------|-----|-----|------|
| Supply voltage | | $V_{CC} = 3.3\text{ V}$ | 3 | 3.3 | 3.6 | V |
| | | $V_{CC} = 5\text{ V}$ | 4.5 | 5 | 5.5 | |
| V_{IH} | Driver and control high-level input voltage | DIN, \overline{EN} , $\overline{PWRDOWN}$ | $V_{CC} = 3.3\text{ V}$ | 2 | | V |
| | | | $V_{CC} = 5\text{ V}$ | 2.4 | | |
| V_{IL} | Driver and control low-level input voltage | DIN, \overline{EN} , $\overline{PWRDOWN}$ | | | 0.8 | V |
| V_I | Driver and control input voltage | DIN, \overline{EN} , $\overline{PWRDOWN}$ | 0 | | 5.5 | V |
| V_I | Receiver input voltage | | -25 | | 25 | V |
| T_A | Operating free-air temperature | SN75C3222E | 0 | | 70 | °C |
| | | SN65C3222E | -40 | | 85 | |

(1) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$.

6.5 Thermal Information: SN65C3222E

| THERMAL METRIC ⁽¹⁾ | | SN65C3222E | | | UNIT |
|-------------------------------|--|------------|-----------|------------|------|
| | | DB (SSOP) | DW (SOIC) | PW (TSSOP) | |
| | | 20 Pins | 20 Pins | 20 Pins | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 70 | 58 | 94.1 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (bottom) thermal resistance | 33.6 | 30.0 | 35.2 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 36.4 | 29.6 | 45.5 | °C/W |
| Ψ_{JT} | Junction-to-top characterization parameter | 4.8 | 7.7 | 3.1 | °C/W |
| Ψ_{JB} | Junction-to-board characterization parameter | 35.9 | 29.3 | 45.1 | °C/W |

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

6.6 Thermal Information: SN75C3222E

| THERMAL METRIC ¹ | | SN75C3222E | | | UNIT |
|-----------------------------|--|------------|-----------|------------|------|
| | | DB (SSOP) | DW (SOIC) | PW (TSSOP) | |
| | | 20 | 20 | 20 | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 70 | 58 | 83 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | 33.6 | 30.0 | 24.8 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 36.4 | 29.6 | 39.5 | °C/W |
| Ψ_{JT} | Junction-to-top characterization parameter | 4.8 | 7.7 | 1.1 | °C/W |
| Ψ_{JB} | Junction-to-board characterization parameter | 35.9 | 29.3 | 39.0 | °C/W |

6.7 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

| PARAMETER | | TEST CONDITIONS ⁽²⁾ | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|-----------|--|---|-----|--------------------|---------|---------------|
| I_I | Input leakage current (\overline{EN} , $\overline{PWRDOWN}$) | | | ± 0.01 | ± 1 | μA |
| I_{CC} | Supply current | No load, $\overline{PWRDOWN}$ at V_{CC} | | 0.3 | 1 | mA |
| | Supply current (powered off) | No load, $\overline{PWRDOWN}$ at GND | | 1 | 10 | μA |

(1) All typical values are at $V_{CC} = 3.3\text{ V}$ or $V_{CC} = 5\text{ V}$, and $T_A = 25^\circ\text{C}$.

(2) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$.

6.8 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

| PARAMETER | | TEST CONDITIONS | | MIN | TYP ⁽¹⁾ (3) | MAX | UNIT |
|-----------------|---|--|---|-----|---------------------------|-----|------|
| V _{OH} | High-level output voltage | DOUT at R _L = 3 kΩ to GND, DIN = GND | | 5 | 5.4 | | V |
| V _{OL} | Low-level output voltage | DOUT at R _L = 3 kΩ to GND, DIN = V _{CC} | | –5 | –5.4 | | V |
| I _{IH} | High-level input current | V _I = V _{CC} | | | ±0.01 | ±1 | μA |
| I _{IL} | Low-level input current | V _I at GND | | | ±0.01 | ±1 | μA |
| I _{OS} | Short-circuit output current ⁽²⁾ | V _{CC} = 3.6 V | V _O = 0 V | | ±35 | ±60 | mA |
| | | V _{CC} = 5.5 V | | | | | |
| r _o | Output resistance | V _{CC} , V ₊ , and V _– = 0 V, V _O = ±2 V | | 300 | 10M | | Ω |
| I _{OZ} | Output leakage current | PWRDOWN = GND | V _{CC} = 3 V to 3.6 V, V _O = ±12 V | | | ±25 | μA |
| | | | V _{CC} = 4.5 V to 5.5 V, V _O = ±10 V | | | ±25 | |

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

(3) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.9 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

| PARAMETER | TEST CONDITIONS ⁽³⁾ | | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|--|--|--|-----|--------------------|-----|--------|
| Maximum data rate (See Figure 7-1) | R _L = 3 kΩ, One DOUT switching | C _L = 1000 pF | | 250 | | kbit/s |
| | | C _L = 250 pF, V _{CC} = 3 V to 4.5 V | | 1000 | | |
| | | C _L = 1000 pF, V _{CC} = 4.5 V to 5.5 V | | 1000 | | |
| t _{sk(p)} | C _L = 150 pF to 2500 pF, R _L = 3 kΩ to 7 kΩ, | See Figure 7-2 | | 300 | | ns |
| SR(tr) Slew rate, transition region (see Figure 7-1) | R _L = 7 kΩ, | C _L = 150 pF to 1000 pF | | 8 | 90 | V/μs |
| | | C _L = 1000 pF | | 12 | 60 | |
| | R _L = 3 kΩ | C _L = 150 pF to 250 pF | | 24 | 150 | |

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Pulse skew is defined as |t_{PLH} – t_{PHL}| of each channel of the same device.

(3) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.10 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

| PARAMETER | | TEST CONDITIONS ⁽²⁾ | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|------------------|---|--------------------------------|-----------------------|-----------------------|-----|------|
| V _{OH} | High-level output voltage | I _{OH} = -1 mA | V _{CC} - 0.6 | V _{CC} - 0.1 | | V |
| V _{OL} | Low-level output voltage | I _{OL} = 1.6 mA | | | 0.4 | V |
| V _{IT+} | Positive-going input threshold voltage | V _{CC} = 3.3 V | | 1.5 | 2.4 | V |
| | | V _{CC} = 5 V | | 1.8 | 2.4 | |
| V _{IT-} | Negative-going input threshold voltage | V _{CC} = 3.3 V | 0.6 | 1.2 | | V |
| | | V _{CC} = 5 V | 0.8 | 1.5 | | |
| V _{hys} | Input hysteresis (V _{IT+} - V _{IT-}) | | | 0.3 | | V |
| I _{OZ} | Output leakage current | EN = 1 | | ±0.05 | ±10 | µA |
| r _i | Input resistance | V _I = ±3 V to ±25 V | 3 | 5 | 7 | kΩ |

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

6.11 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

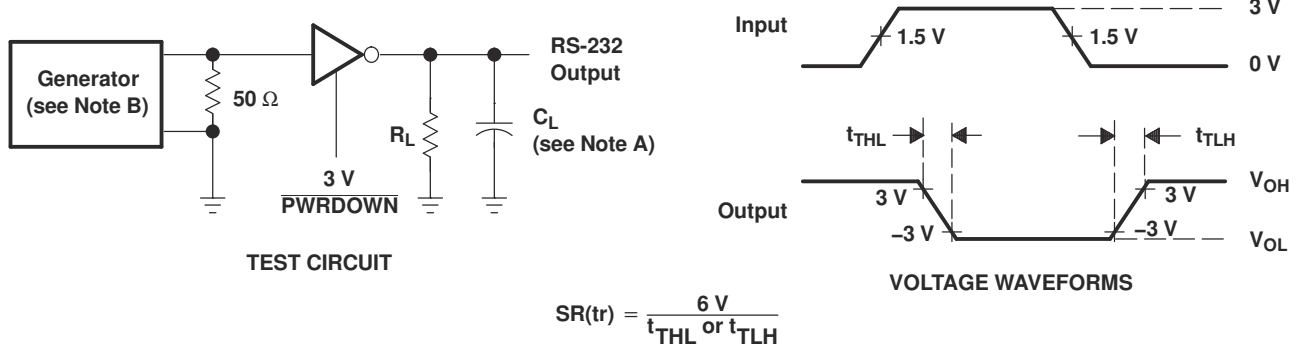
| PARAMETER | | TEST CONDITIONS ⁽³⁾ | TYP ⁽¹⁾ | UNIT |
|--------------------|---|--|--------------------|------|
| t _{PLH} | Propagation delay time, low- to high-level output | C _L = 150 pF, See Figure 7-3 | 300 | ns |
| t _{PHL} | Propagation delay time, high- to low-level output | C _L = 150 pF, See Figure 7-3 | 300 | ns |
| t _{en} | Output enable time | C _L = 150 pF, R _L = 3 kΩ, See Figure 7-4 | 200 | ns |
| t _{dis} | Output disable time | C _L = 150 pF, R _L = 3 kΩ, See Figure 7-4 | 200 | ns |
| t _{sk(p)} | Pulse skew ⁽²⁾ | See Figure 7-3 | 300 | ns |

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

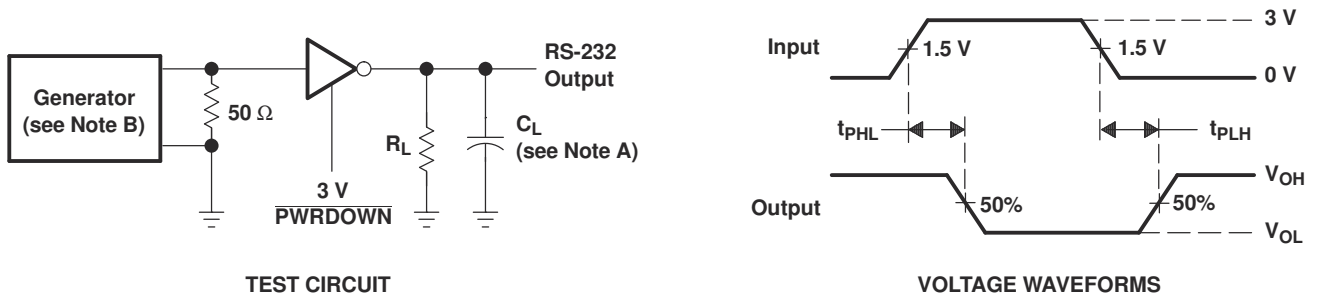
(3) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

7 Parameter Measurement Information



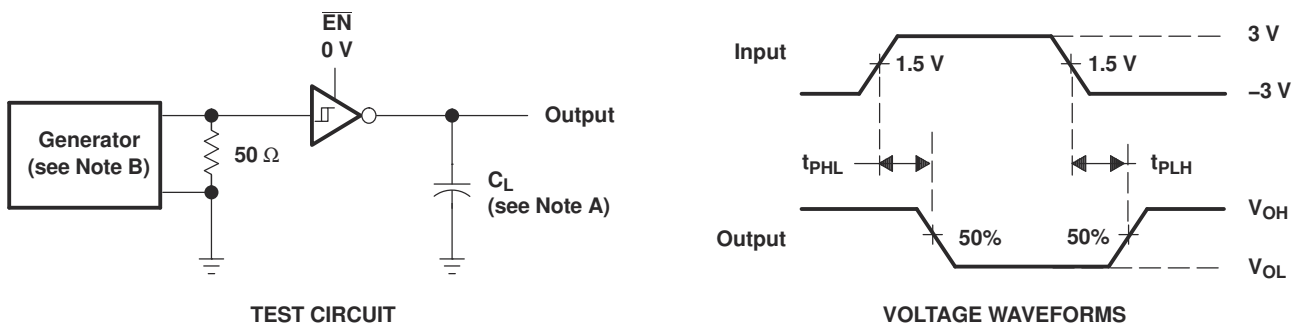
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 7-1. Driver Slew Rate



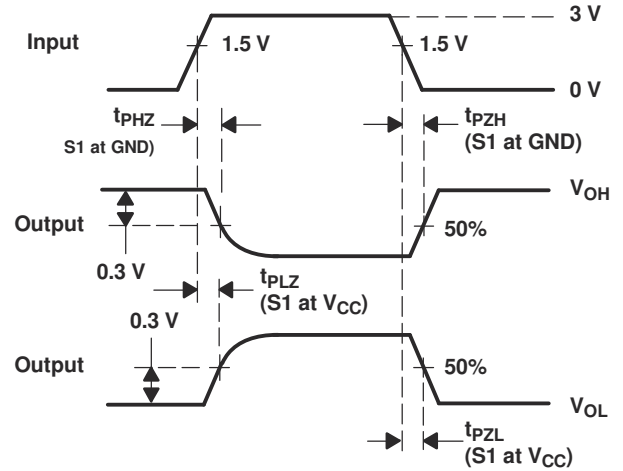
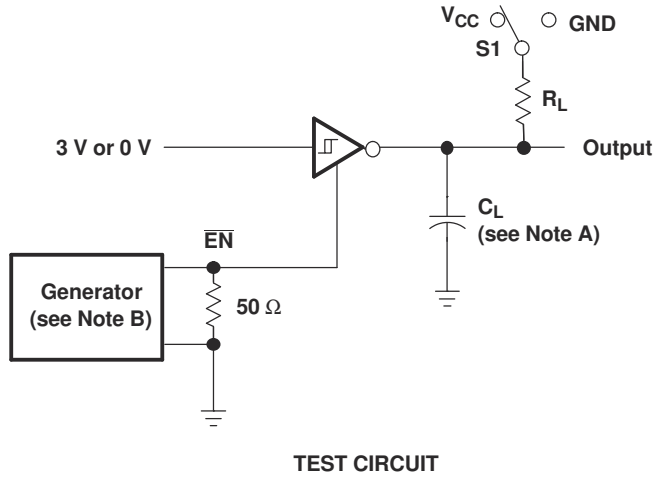
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 7-2. Driver Pulse Skew



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 7-3. Receiver Propagation Delay Times

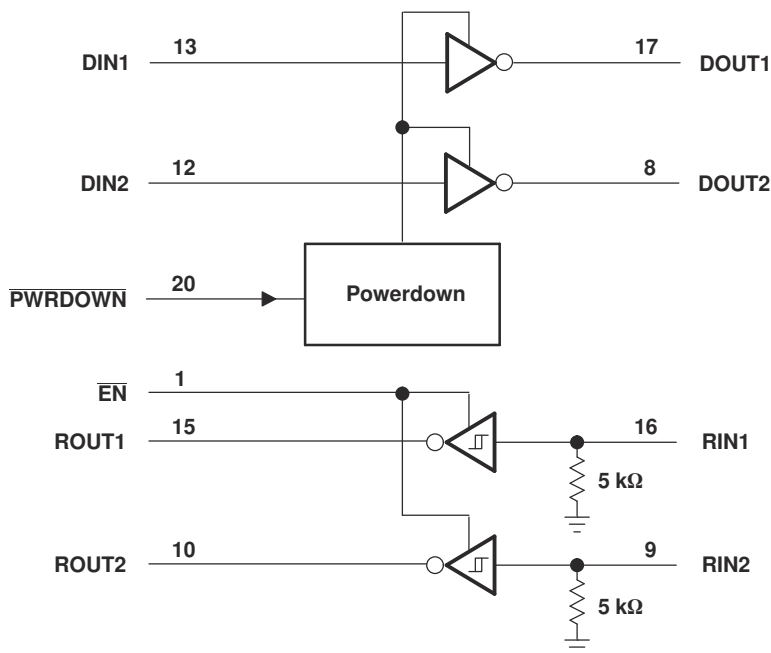


- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\ \text{ns}$, $t_f \leq 10\ \text{ns}$.

Figure 7-4. Receiver Enable and Disable Times

8 Detailed Description

8.1 Functional Block Diagram



Pin numbers are for the DB, DW, and PW packages.

Figure 8-1. Logic Diagram (Positive Logic)

8.2 Device Functional Modes

Table 8-1. Function Tables: Each Driver

| INPUTS ⁽¹⁾ | | OUTPUT DOUT |
|-----------------------|---------|----------------|
| DIN | PWRDOWN | |
| X | L | Z |
| L | H | H |
| H | H | L |

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Table 8-2. Function Table: Each Receiver

| INPUTS ⁽¹⁾ | | OUTPUT ROUT |
|-----------------------|----|----------------|
| RIN | EN | |
| L | L | H |
| H | L | L |
| X | H | Z |
| Open | L | H |

(1) H = high level, L = low level, X = irrelevant,
 Z = high impedance (off),
 Open = input disconnected or connected driver off

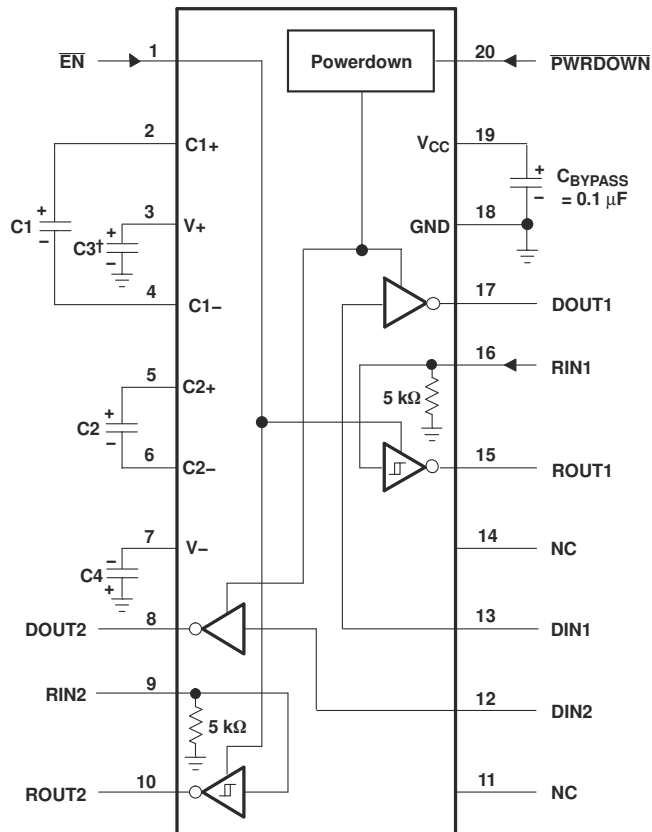
9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

9.2 Typical Application



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. NC – No internal connection

C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

| V _{CC} | C1 | C2, C3, and C4 |
|-----------------|----------|----------------|
| 3.3 V ± 0.3 V | 0.1 μF | 0.1 μF |
| 5 V ± 0.5 V | 0.047 μF | 0.33 μF |
| 3 V to 5.5 V | 0.1 μF | 0.47 μF |

Figure 9-1. Typical Operating Circuit and Capacitor Values

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|-------------------------|
| SN65C3222EDB | ACTIVE | SSOP | DB | 20 | 70 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | MU222E | Samples |
| SN65C3222EDBR | ACTIVE | SSOP | DB | 20 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | MU222E | Samples |
| SN65C3222EDW | ACTIVE | SOIC | DW | 20 | 25 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 65C3222E | Samples |
| SN65C3222EDWR | ACTIVE | SOIC | DW | 20 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 65C3222E | Samples |
| SN65C3222EPWR | NRND | TSSOP | PW | 20 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | MU222E | |
| SN75C3222EPW | OBSOLETE | TSSOP | PW | 20 | | TBD | Call TI | Call TI | 0 to 70 | MY222E | |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| SN65C3222EDBR | SSOP | DB | 20 | 2000 | 330.0 | 16.4 | 8.2 | 7.5 | 2.5 | 12.0 | 16.0 | Q1 |
| SN65C3222EDWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.3 | 2.7 | 12.0 | 24.0 | Q1 |
| SN65C3222EPWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.0 | 1.4 | 8.0 | 16.0 | Q1 |
| SN65C3222EPWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.0 | 1.4 | 8.0 | 16.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

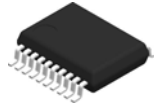
| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN65C3222EDBR | SSOP | DB | 20 | 2000 | 356.0 | 356.0 | 35.0 |
| SN65C3222EDWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |
| SN65C3222EPWR | TSSOP | PW | 20 | 2000 | 356.0 | 356.0 | 35.0 |
| SN65C3222EPWR | TSSOP | PW | 20 | 2000 | 356.0 | 356.0 | 35.0 |

TUBE


*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|--------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| SN65C3222EDB | DB | SSOP | 20 | 70 | 530 | 10.5 | 4000 | 4.1 |
| SN65C3222EDW | DW | SOIC | 20 | 25 | 507 | 12.83 | 5080 | 6.6 |

DB0020A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



4214851/B 08/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

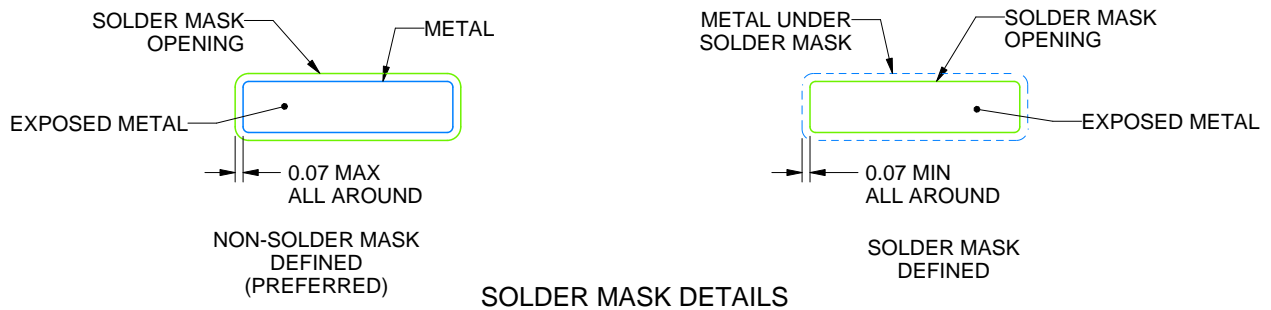
DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4214851/B 08/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

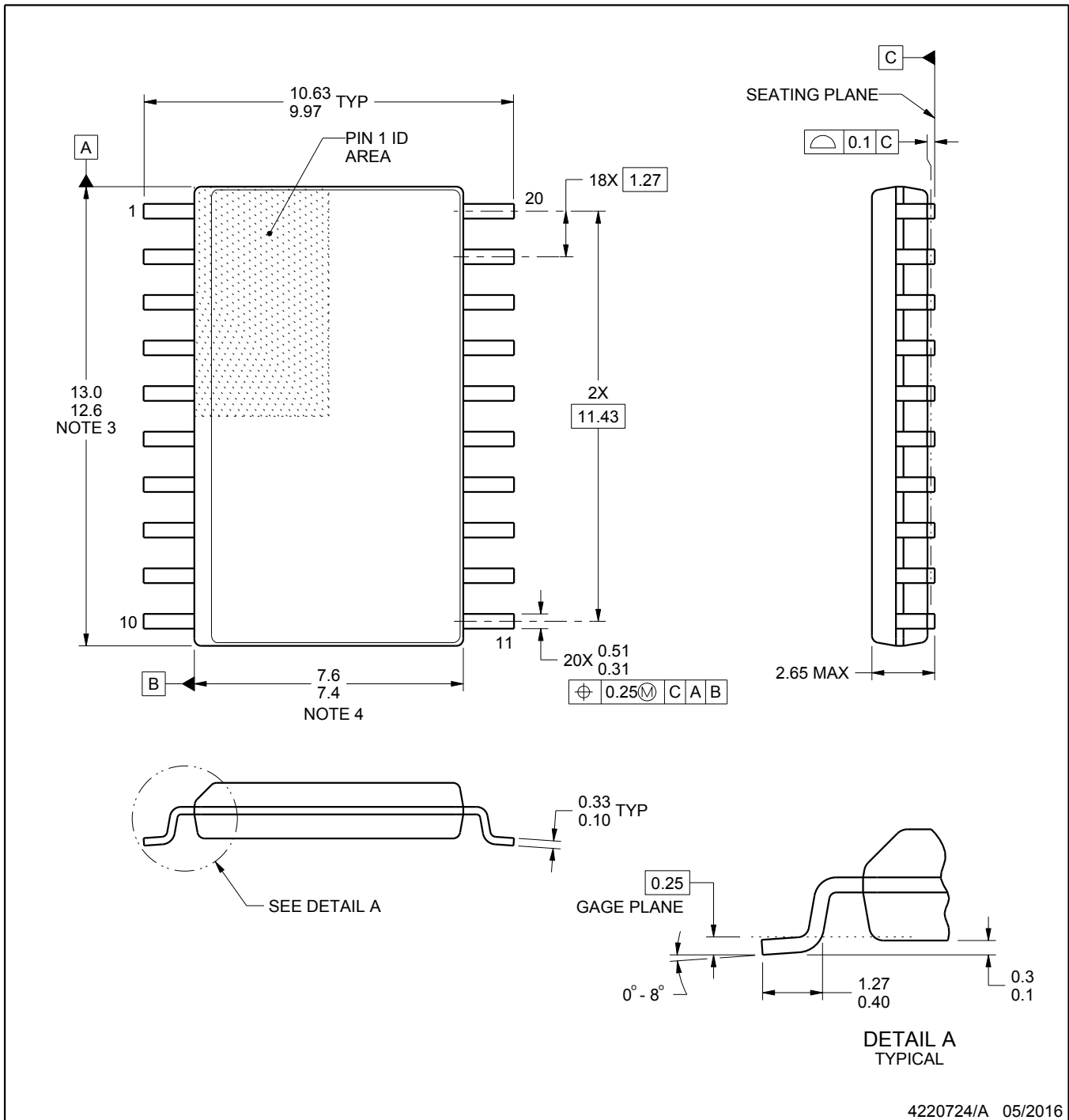
DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4220724/A 05/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW0020A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220206/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220206/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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